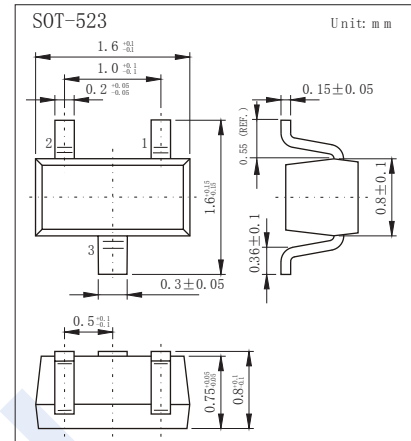
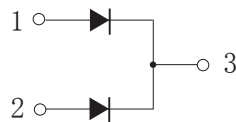


Switching Diodes

DAN222 (KAN222)

■ Features

- Four types of packaging are available
- High speed
- Suitable for high packing density layout
- High reliability

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Peak Reverse Voltage	V_{RM}	80	V
DC Reverse Voltage	V_R	80	
Average forward current	I_O	100	mA
Peak Forward Surge Current	I_{FM}	300	
Power Dissipation	P_d	150	mW
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Reverse breakdown voltage	V_R	$I_R = 100 \mu\text{A}$	80			V
Forward voltage	V_F	$I_F = 100\text{mA}$			1.2	
Reverse voltage leakage current	I_R	$V_R = 70 \text{V}$			0.1	μA
Junction capacitance	C_j	$V_R = 6 \text{V}, f = 1 \text{MHz}$			3.5	pF
Reverse recovery time	t_{rr}	$I_F = I_R = 5\text{mA}, V_R = 6\text{V}$			4	ns

■ Marking

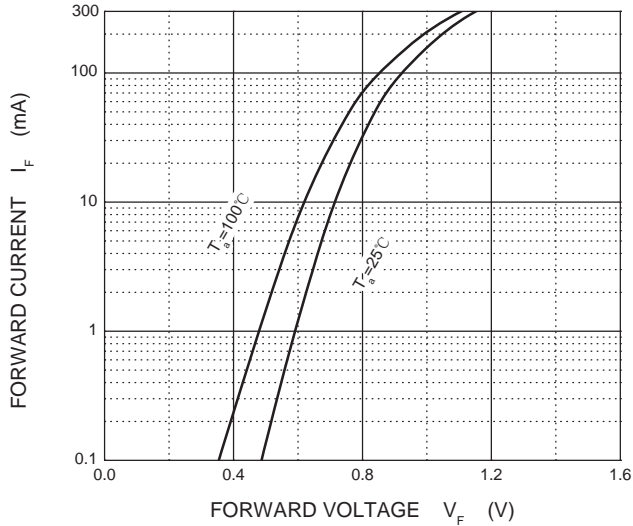
Marking	N

Switching Diodes

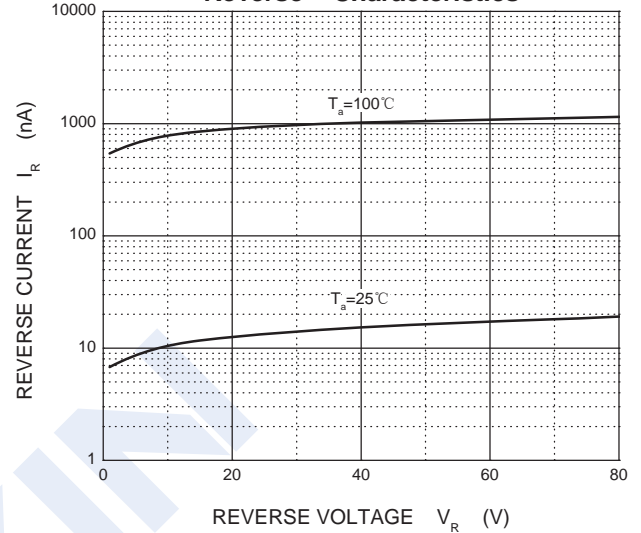
DAN222 (KAN222)

■ Typical Characteristics

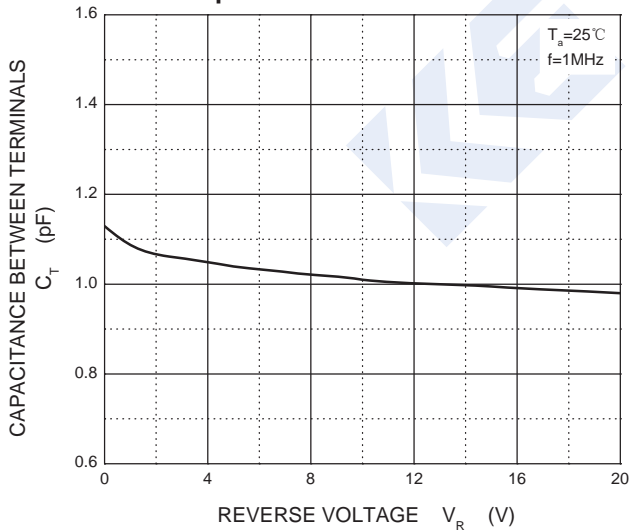
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

